

# MPS6729

Preferred Device

## One Watt Amplifier Transistor

PNP Silicon

### Features

- Pb-Free Package is Available\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-80	Vdc
Collector-Base Voltage	$V_{CBO}$	-80	Vdc
Emitter-Base Voltage	$V_{EBO}$	-4.0	Vdc
Collector Current - Continuous	$I_C$	-500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.0 8.0	W mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	2.5 20	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

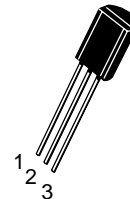
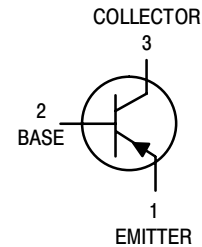
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



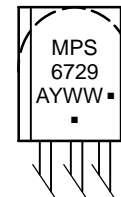
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<http://onsemi.com>



TO-92 (TO-226)  
CASE 29-10  
STYLE 1

### MARKING DIAGRAM



MPS6729 = Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping
MPS6729	TO-92	5000 Units / Bulk
MPS6729G	TO-92 (Pb-Free)	5000 Units / Bulk

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

# MPS6729

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 1) ( $I_C = -1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-80	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 0.1\text{ mA}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-80	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -10\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CB} = -60\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-0.1	$\mu\text{A}$ dc
Emitter Cutoff Current ( $V_{EB} = -5.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	-10	$\mu\text{A}$ dc
<b>ON CHARACTERISTICS (Note 1)</b>				
DC Current Gain ( $I_C = -50\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -250\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ )	$h_{FE}$	80 50	- 250	-
Collector–Emitter Saturation Voltage ( $I_C = -250\text{ mA}$ , $I_B = -10\text{ mA}$ )	$V_{CE(sat)}$	-	-0.5	Vdc
Base–Emitter On Voltage ( $I_C = -250\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ )	$V_{BE(on)}$	-	-1.2	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Collector–Base Capacitance ( $V_{CB} = -10\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{cb}$	-	30	pF
Small–Signal Current Gain ( $I_C = 200\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ , $f = 20\text{ MHz}$ )	$h_{fe}$	2.5	25	

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

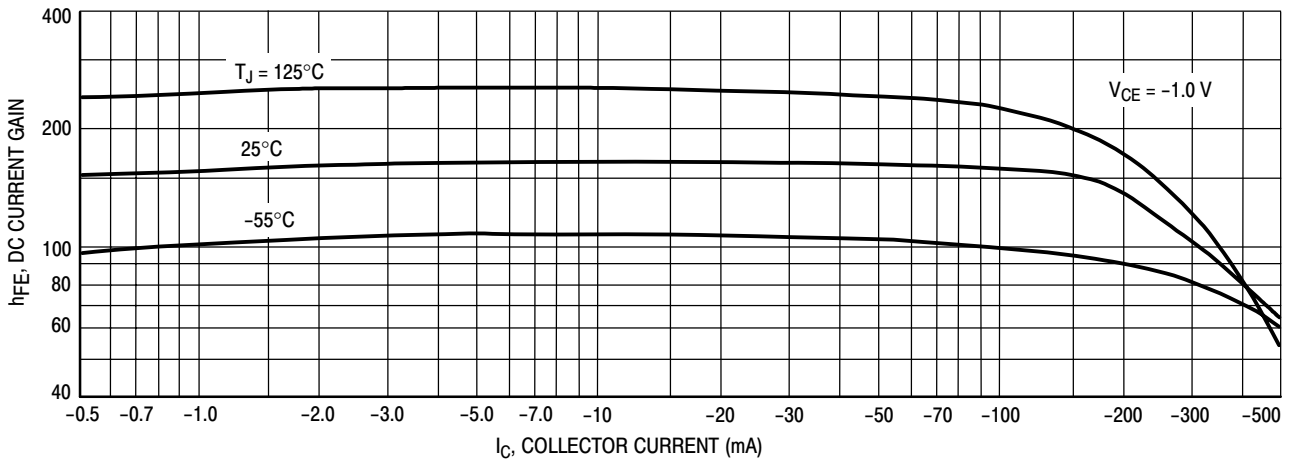


Figure 1. DC Current Gain

# MPS6729

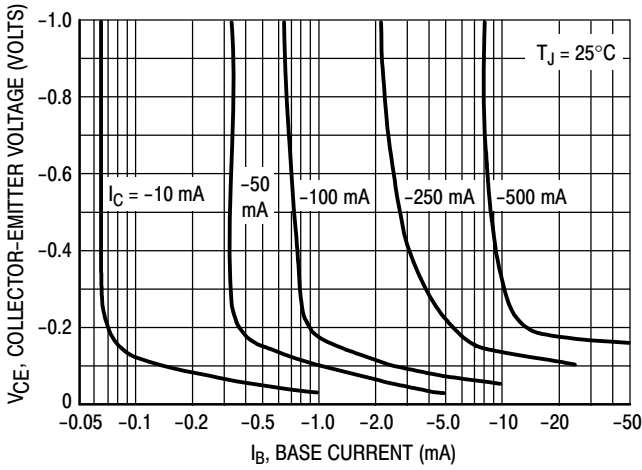


Figure 2. Collector Saturation Region

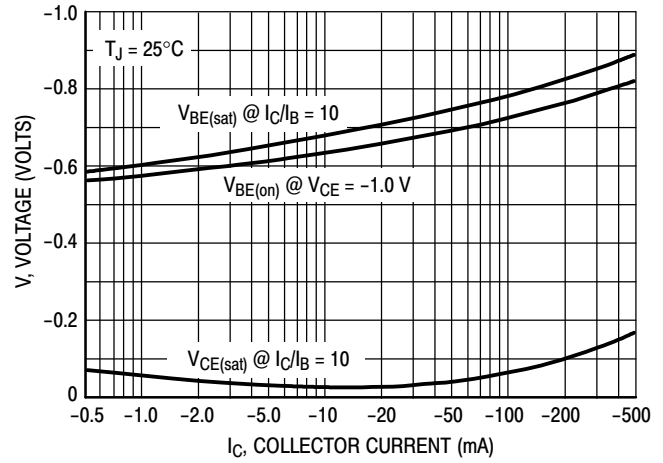


Figure 3. "On" Voltages

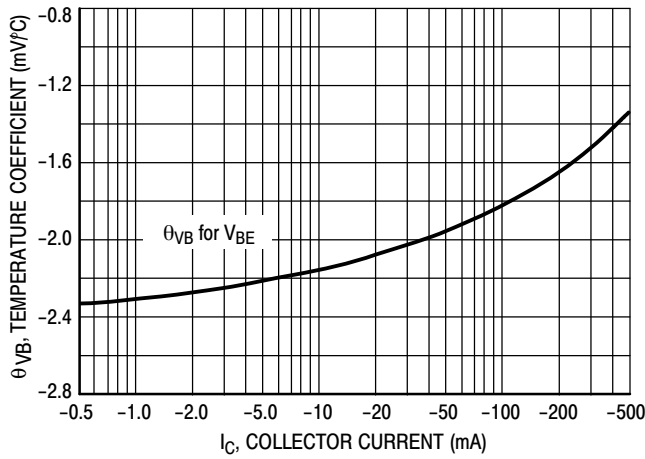


Figure 4. Base-Emitter Temperature Coefficient

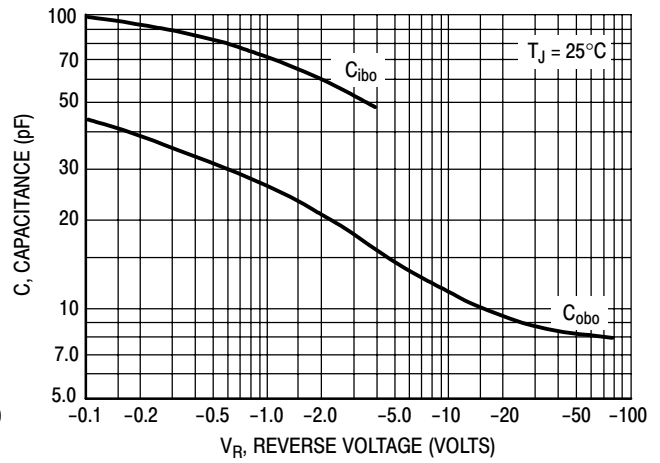


Figure 5. Capacitance

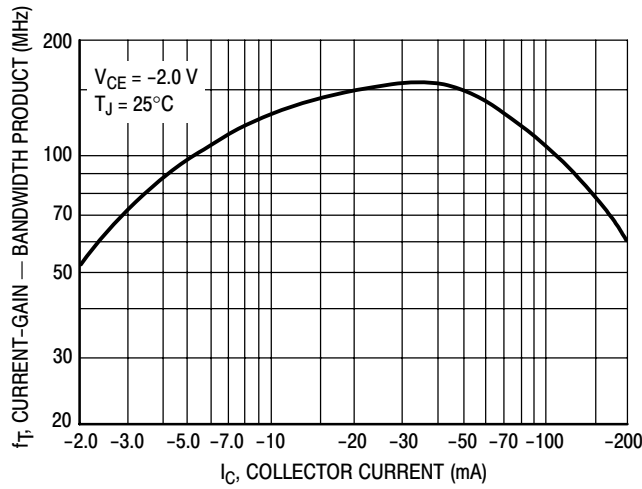


Figure 6. Current-Gain - Bandwidth Product

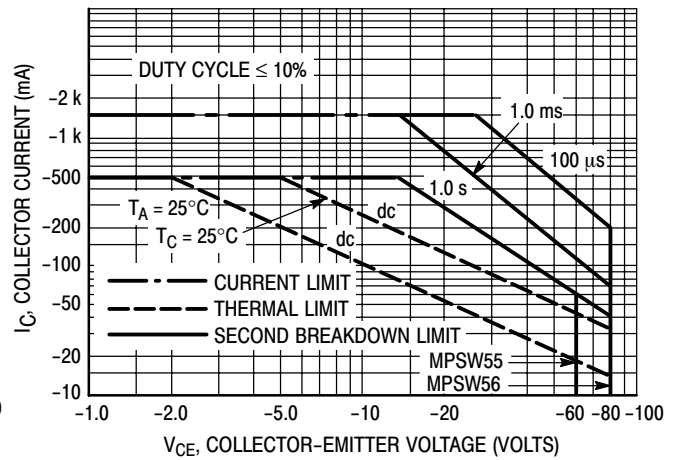
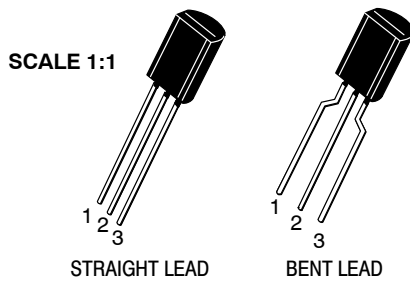


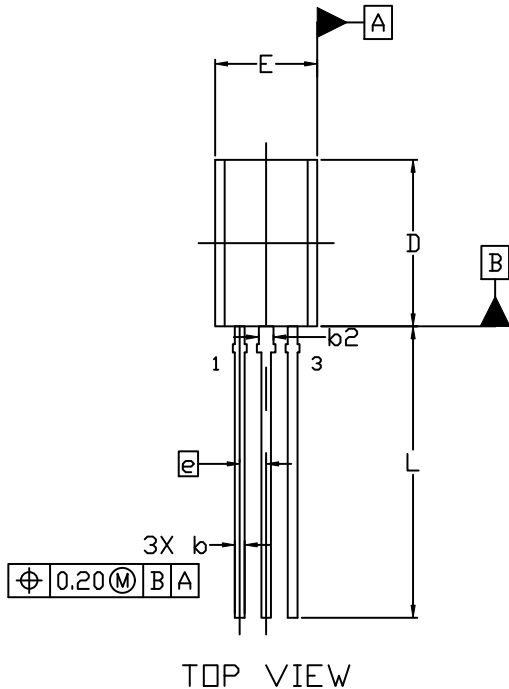
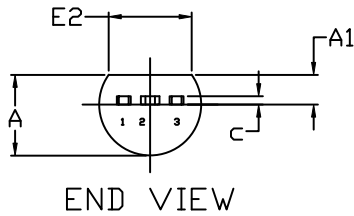
Figure 7. Active Region - Safe Operating Area



**TO-92 (TO-226) 1 WATT**  
**CASE 29-10**  
**ISSUE D**

DATE 05 MAR 2021

**STRAIGHT LEAD**



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	1.27 BSC		
L	13.80	14.00	14.20

**STYLES AND MARKING ON PAGE 3**

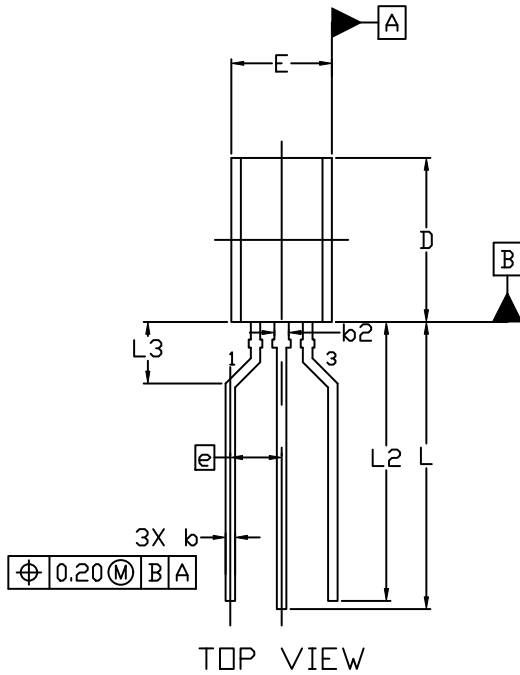
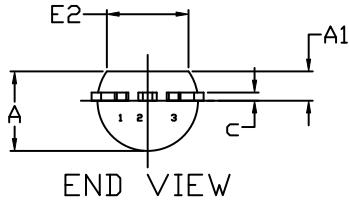
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TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE D

DATE 05 MAR 2021

FORMED LEAD



NOTES:

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D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3	3.00 REF		

STYLES AND MARKING ON PAGE 3

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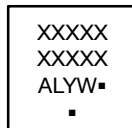
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**TO-92 (TO-226) 1 WATT  
CASE 29-10  
ISSUE D**

DATE 05 MAR 2021

- |   |  |  |   |   |
|---|--|--|---|---|
| STYLE 1:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR           | STYLE 2:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR                | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE           | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE            | STYLE 5:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE            |
| STYLE 6:<br>PIN 1. GATE<br>2. SOURCE & SUBSTRATE<br>3. DRAIN    | STYLE 7:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE                     | STYLE 8:<br>PIN 1. DRAIN<br>2. GATE<br>3. SOURCE & SUBSTRATE | STYLE 9:<br>PIN 1. BASE 1<br>2. EMITTER<br>3. BASE 2            | STYLE 10:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          |
| STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE & ANODE<br>3. CATHODE   | STYLE 12:<br>PIN 1. MAIN TERMINAL 1<br>2. GATE<br>3. MAIN TERMINAL 2 | STYLE 13:<br>PIN 1. ANODE 1<br>2. GATE<br>3. CATHODE 2       | STYLE 14:<br>PIN 1. EMITTER<br>2. COLLECTOR<br>3. BASE          | STYLE 15:<br>PIN 1. ANODE 1<br>2. CATHODE<br>3. ANODE 2     |
| STYLE 16:<br>PIN 1. ANODE<br>2. GATE<br>3. CATHODE              | STYLE 17:<br>PIN 1. COLLECTOR<br>2. BASE<br>3. EMITTER               | STYLE 18:<br>PIN 1. ANODE<br>2. CATHODE<br>3. NOT CONNECTED  | STYLE 19:<br>PIN 1. GATE<br>2. ANODE<br>3. CATHODE              | STYLE 20:<br>PIN 1. NOT CONNECTED<br>2. CATHODE<br>3. ANODE |
| STYLE 21:<br>PIN 1. COLLECTOR<br>2. EMITTER<br>3. BASE          | STYLE 22:<br>PIN 1. SOURCE<br>2. GATE<br>3. DRAIN                    | STYLE 23:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN            | STYLE 24:<br>PIN 1. EMITTER<br>2. COLLECTOR/ANODE<br>3. CATHODE | STYLE 25:<br>PIN 1. MT 1<br>2. GATE<br>3. MT 2              |
| STYLE 26:<br>PIN 1. V <sub>CC</sub><br>2. GROUND 2<br>3. OUTPUT | STYLE 27:<br>PIN 1. MT<br>2. SUBSTRATE<br>3. MT                      | STYLE 28:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE           | STYLE 29:<br>PIN 1. NOT CONNECTED<br>2. ANODE<br>3. CATHODE     | STYLE 30:<br>PIN 1. DRAIN<br>2. GATE<br>3. SOURCE           |
| STYLE 31:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE               | STYLE 32:<br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER               | STYLE 33:<br>PIN 1. RETURN<br>2. INPUT<br>3. OUTPUT          | STYLE 34:<br>PIN 1. INPUT<br>2. GROUND<br>3. LOGIC              | STYLE 35:<br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER      |

**GENERIC  
MARKING DIAGRAM\***



- XXXX = Specific Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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